

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND
PROGRAM

ABSTRACT

There is provided a technique that includes: performing a first step and a second step a predetermined number of times, wherein the first step includes performing a predetermined number of times: (a1) supplying a first modifying gas to the substrate to form a first modified layer on at least a portion of the substrate; and (a2) supplying a first removal gas to the substrate to remove a portion of the first modified layer from the substrate, and wherein the second step includes performing, after the first step, a predetermined number of times: (b1) supplying a process gas to the substrate to preferentially process an area where the first modified layer is not formed over an area where the first modified layer is present; and (b2) supplying a reactant gas to the substrate.

FIGs. 5C and 5D